

ABSTRACT OF THE DISCLOSURE

A magnetic memory device comprises a plurality of magneto-resistance effect elements arranged in a matrix form. The each of a plurality of magneto-resistance  
5 effect elements have a pattern shape which substantially internally touches an ellipse having major and minor axes of the magneto-resistance effect element as major and minor axes thereof and a pitch between the adjacent magneto-resistance effect elements in  
10 a direction of the major axis is longer than that in a direction of the minor axis.